



# <span id="page-0-0"></span>**1. Description**

The PIP250M is a fully integrated synchronous buck converter intended for use as a point-of-load regulator. It contains two N-channel power MOSFETs, a Schottky diode and a voltage mode, pulse width modulated (PWM) controller. The controller features include overcurrent and overvoltage protection and undervoltage lockout functions. By combining the power components and the controller into a single component, stray inductances are virtually eliminated, resulting in lower switching losses and a compact, efficient design with minimal external component count.

### <span id="page-0-1"></span>**2. Features**

- Output current up to 15 A
- Single supply 5 V operation
- Fixed 300 kHz operating frequency
- Voltage mode control
- Minimum regulated output voltage 0.8 V
- Internal soft start
- Overcurrent protection
- Overvoltage protection
- Remote sensing.

### <span id="page-0-2"></span>**3. Applications**

- High-current point-of-load regulation
- Distributed power architectures
- Multiple output telecom power supplies
- Microprocessor and Digital Signal Processing (DSP) supplies
- Computer peripheral supplies
- Cable modems
- Set-top boxes.

### <span id="page-0-3"></span>**4. Ordering information**

#### **Table 1: Ordering information**







### <span id="page-1-1"></span>**5. Block diagram**

<span id="page-1-0"></span>

# <span id="page-2-2"></span><span id="page-2-1"></span>**6. Pinning information**

#### Grey area denotes terminal 1 index area. **Fig 2. Pin configuration (footprint view).** VO PAD 3 **PIP250M** V<sub>DDO</sub> PAD 2 V<sub>SSC</sub> P<sub>AD</sub><sub>1</sub> 18 19 20 21 22 23 24 25 26 27 28 29 30 31 32 33 34 68 67 66 65 64 63 62 61 60 59 58 57 56 55 54 53 52  $\overline{2}$  $\overline{1}$  $\boxed{3}$  $\boxed{4}$  $\boxed{5}$  $\boxed{6}$ <u>ক</u>  $\overline{7}$ 11) 8 10  $\overline{12}$ 14 <sup>V</sup>DDO 16 13) 15 <sup>V</sup>DDO <sup>17</sup> 50 Vsso  $\overline{51}$ 49 VSSO 48 VSSO 47 VSSO  $\sqrt{46}$  $\overline{43}$  $\overline{45}$ 41 VO 44 42 VSSO 40 38 36 39 37  $\overline{35}$ 03aj53 CB VO n.c. n.c. OCSET/ENABLE OCSET/ENABLE PHASE n.c. V<sub>DDO</sub> V<sub>SSC</sub> V<sub>DDO</sub> n.c. V<sub>DDO</sub> V<sub>DDO</sub>  $V<sub>DDO</sub>$ 999999 VO 888888<br>Po VO VO VO VO XSC = 0<br>VSSC = 0<br>VSSC = 0<br>VSSC = 0<br>VSSC = 0<br>VSSC = 0<br>VSSC = 00000000<br>VSSC = 00000000  $V$ SSO  $V$ SSO  $V_{\text{SSO}}$ VSSO V<sub>SSO</sub> VO VO VO VO VO VO

### <span id="page-2-3"></span>**6.2 Pin description**

<span id="page-2-0"></span>

### **6.1 Pinning**

- <span id="page-3-0"></span>[1] PAD1, PAD2 and PAD3 are electrical connections and must be soldered to the printed circuit board
- <span id="page-3-1"></span>[2] All n.c. pins should be connected to  $V_{SSC}$ .

### <span id="page-3-4"></span><span id="page-3-3"></span><span id="page-3-2"></span>**7. Functional description**

### **7.1 Pin functions**

#### **7.1.1 Output stage supply (V<sub>DDO</sub>, V<sub>SSO</sub>)**

The power output stage of the PIP250M consists of two N-channel, power MOSFETs and a Schottky diode configured as a synchronous buck converter. The drain of the upper MOSFET is connected to the positive conversion supply  $(V_{DDO})$ , and the source of the lower MOSFET is connected to power ground  $(V_{SSO})$ . The Schottky diode is connected between the source and drain of the lower MOSFET.

#### <span id="page-3-5"></span>**7.1.2 Output voltage (VO)**

VO is the switched node of the power MOSFET output stage. This node is connected internally to the source of the upper MOSFET and the drain of the lower MOSFET.

#### <span id="page-3-6"></span>**7.1.3 Control circuit supply (V<sub>DDC</sub>, V<sub>SSC</sub>)**

 $V_{\text{DDC}}$  is the positive supply to the control circuit.  $V_{\text{SSC}}$  is the control circuit ground. All control voltages are measured with respect to  $V_{SSC}$ .

#### <span id="page-3-7"></span>**7.1.4 Bootstrap capacitor connection (CB)**

The upper MOSFET driver stage is powered from the CB pin.

#### <span id="page-3-8"></span>**7.1.5 Voltage feedback pin (FB)**

The FB pin is connected to the inverting input of the error amplifier, and to the inputs of the overvoltage and undervoltage comparators.

#### <span id="page-3-9"></span>**7.1.6 Current limit set and enable input (OCSET/ENABLE)**

The overcurrent threshold is set by an external resistor between  $V_{DDO}$  and OCSET/ENABLE. The PIP250M can be shut down by pulling this pin LOW.

#### <span id="page-3-10"></span>**7.1.7 Sense connection for current limit (PHASE)**

The PHASE input is normally connected externally to the power output stage switched node (VO). The voltage on the PHASE input is compared with the voltage on the OCSET/ENABLE input during the interval when the upper MOSFET is on. The overcurrent trip operates if the voltage on the PHASE input is lower than the voltage on the OCSET/ENABLE input.

### **7.2 Operation**

#### <span id="page-4-2"></span><span id="page-4-1"></span>**7.2.1 Single supply operation**



<span id="page-4-0"></span>Operation of the PIP250M from a single 5 V conversion supply is shown in [Figure 3](#page-4-0). The upper MOSFET gate driver stage is supplied from the CB pin. An external bootstrap circuit, comprising D1 and the 100 nF capacitor generates a voltage on CB of twice  $V<sub>DDO</sub>$ .

The control circuit supply,  $V_{\text{DDC}}$  is protected from transients by a low pass filter comprising a 10 Ω resistor and a 1  $\mu$ F capacitor. These components should be placed close to the device pins.

#### <span id="page-4-3"></span>**7.2.2 Regulated output voltage**

The reference voltage of the PIP250M is 0.8 V. The regulated output voltage is set using a resistive divider as shown in [Figure 9.](#page-10-0) The resistors should be placed as close as possible to the FB pin. Both resistors should be less than 1  $k\Omega$  in order to avoid noise coupling. The 68 nF capacitor across the upper resistor improves the control loop stability by adding a small amount of phase margin.

#### <span id="page-4-4"></span>**7.2.3 Power on reset**

The PIP250M control circuit powers up when the voltage on  $V_{DDC}$  rises above the start-up threshold voltage (typically 4.1 V). The control circuit stops operating when the voltage on  $V_{\text{DDC}}$  falls below the power-down threshold voltage (typically 3.6 V).

Once the voltage on  $V_{DDC}$  is above the start-up threshold voltage, the PIP250M does not produce pulses until the voltage on OCSET/ENABLE rises above the OCSET/ ENABLE start-up threshold voltage (typically 1.25 V).

#### <span id="page-4-5"></span>**7.2.4 Soft start**

The soft start sequence prevents surge currents being drawn from the conversion supply when the PIP250M is powered up into a high current load. The soft start sequence is controlled by an internal digital counter. During the soft start sequence, the reference voltage on the non inverting input of the error amplifier is increased from zero up to the normal operating level of 0.8 V. The duration of the soft start sequence is typically 2 ms.

### <span id="page-5-1"></span>**7.2.5 Overcurrent protection**



<span id="page-5-0"></span>The overcurrent protection function is shown in [Figure 4.](#page-5-0) The overcurrent trip function is enabled when the upper MOSFET gate drive signal is HIGH.

During this interval, the voltage on the PHASE input is compared with the voltage on the OCSET/ENABLE input. If the voltage on the PHASE input is lower than the voltage on the OCSET/ENABLE input, then the PIP250M detects an overcurrent trip condition and turns off the gate drive to the upper MOSFET. There is an internal filter with a time constant of 30  $\mu$ s in series with the PHASE input. Since the switching frequency is 300 kHz, this means that the overcurrent trip operates if the overcurrent condition persists for10 switching cycles.

If three overcurrent pulses are detected, the PIP250M latches off and produces no more pulses until it has been reset. To reset the PIP250M, the supply voltage  $(V_{\text{DDC}})$ must be reduced below the power down reset threshold and then increased back up to 5 V.

An external resistor ( $R_{OCSFT}$ ) sets the overcurrent trip level. [Figure 5](#page-6-0) shows the overcurrent trip level ( $I_{TRIP}$ ) as a function of  $R_{OCSET}$ .



#### <span id="page-6-1"></span><span id="page-6-0"></span>**7.2.6 Undervoltage and overvoltage protection**

With reference to [Figure 1](#page-1-0), the FB pin is connected internally to the overvoltage and undervoltage comparators, labelled OVP and UVP respectively. In normal operation, the voltage on FB is regulated at 0.8 V.

If the voltage on FB exceeds the overvoltage protection (OVP) threshold (1 V) for longer than 30 µs, an overvoltage condition is detected, the gate drive signals to the MOSFETs are disabled, and the PIP250M latches off. To reset the latch, the PIP250M must be powered down by reducing  $V_{\text{DDC}}$  below the power down reset threshold and then increasing  $V_{\text{DDC}}$  back up to 5 V.

If the voltage on FB drops below the undervoltage protection (UVP) threshold (0.5 V) for longer than 30  $\mu$ s, then an undervoltage condition is detected and the gate drive signals to the MOSFET drivers are turned off. If three undervoltage pulses are detected then the PIP250M latches off. To reset the PIP250M, the supply voltage  $(V_{DDC})$  must be reduced below the power down reset threshold and then increased back up to 5 V.

# <span id="page-7-4"></span>**8. Limiting values**

#### **Table 3: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).



<span id="page-7-2"></span>[1] Pulse width and repetition rate limited by maximum value of  $T_i$ .

<span id="page-7-3"></span>[2] Assumes a thermal resistance from junction to printed-circuit board of 5 K/W

<span id="page-7-0"></span>[3] The PIP250M meets class 2 for Human Body Model and class M3 for Machine Model.

<span id="page-7-1"></span>

# <span id="page-8-1"></span>**9. Thermal characteristics**



# <span id="page-8-2"></span>**10. Characteristics**

#### <span id="page-8-0"></span>**Table 5: Characteristics**

 $V_{DDC}$  = 5 V; T<sub>amb</sub> = 25 °C; circuit of [Figure](#page-10-0) 9 unless otherwise specified.

| <b>Symbol</b>                        | <b>Parameter</b>  | <b>Conditions</b>   | <b>Min</b>               | <b>Typ</b> | <b>Max</b>     | <b>Unit</b> |
|--------------------------------------|---|---|--------------------------|------------|----------------|-------------|
| <b>Control circuit supply</b>        |   |   |                          |            |                |             |
| <b>V<sub>DDC</sub></b>               | control circuit supply voltage $-40 °C \le T_i \le +125 °C$ |   | $\overline{\phantom{a}}$ | 5          | $\blacksquare$ | V           |
| <b>I</b> <sub>DDC</sub>              | control circuit supply current                              |   |                          | 24         |                | mA          |
| <b>Power dissipation</b>             |   |   |                          |            |                |             |
| $P_{\text{tot}}$                     | power dissipation   | $V_{DDC} = 5 V$ ; $V_{DDO} = 5 V$ ;<br>$V_{\text{O}} = 2.5$ V; $I_{\text{O(AV)}} = 15$ A;<br>Figure 7 |                          | 3.6        |                | W           |
| η                                    | efficiency  | $V_{\text{DDC}} = 5 V$ ; $V_{\text{DDO}} = 5 V$ ;<br>$V_O = 2.5$ V; $I_{O(AV)} = 15$ A;<br>Figure 8   |                          | 88         |                | $\%$        |
| <b>Power-on Reset</b>                |   |   |                          |            |                |             |
| $V_{\text{DDC}(\text{th})\text{su}}$ | start-up threshold control<br>circuit supply voltage        | $V_{\text{DDC}}$ increasing:<br>$V_{OCSET}$ = 4.5 V   | 3.85                     | 4.1        | 4.35           | V           |
| $V_{\text{DDC(th)}sd}$               | shut-down threshold control<br>circuit supply voltage       | V <sub>DDC</sub> decreasing;<br>$V_{OCSET}$ = 4.5 V   | 3.25                     | 3.7        | 3.98           | $\vee$      |
| V <sub>hys</sub>                     | hysteresis  | $V_{OCSET}$ = 4.5 V   | 0.3                      | 0.5        | 0.7            | $\vee$      |
| $V$ OCSET(th)su                      | start-up threshold voltage<br><b>OCSET</b>                  | V <sub>OCSET</sub> increasing   | 0.8                      | 1.25       | 2.0            | $\vee$      |
| <b>Reference</b>                     |   |   |                          |            |                |             |
| $V_{i(ref)FB}$                       | reference voltage   | measured at FB pin  | 0.78                     | 0.8        | 0.82           | $\vee$      |
| <b>Oscillator</b>                    |   |   |                          |            |                |             |
| $f_{\rm osc}$                        | oscillator frequency  |   | 250                      | 300        | 350            | kHz         |
| $V_{\text{osc}(p-p)}$                | oscillator ramp amplitude<br>(peak-to-peak value)           |   | ٠                        | 1.75       | ۰              | V           |

**Integrated buck converter**

#### **Table 5: Characteristics**…continued

 $V_{DDC}$  = 5 V;  $T_{amb}$  = 25 °C; circuit of Figure 9 unless otherwise specified.



<span id="page-9-1"></span><span id="page-9-0"></span>

# <span id="page-10-1"></span>**11. Application information**

<span id="page-10-0"></span>

## <span id="page-11-1"></span>**12. Marking**

<span id="page-11-0"></span>![](_page_11_Figure_3.jpeg)

## <span id="page-12-0"></span>**13. Package outline**

![](_page_12_Figure_3.jpeg)

**HVQFN68: plastic thermal enhanced very thin quad flat package; no leads; 68 terminals; body 10 x 10 x 0.85 mm**

**SOT687-1**

#### **Fig 12. SOT687-1.**

### <span id="page-13-3"></span><span id="page-13-2"></span>**14. Soldering**

### **14.1 Introduction to soldering HVQFN packages**

The HVQFN package is a near Chip Scale Package (CSP) with a copper lead frame. It is a leadless package, where electrical contact to the printed circuit board is made through metal pads on the underside of the package. In addition to the small pads around the periphery of the package, there are large pads on the underside that provide low thermal resistance, low electrical resistance, low inductance connections between the power components inside the package and the PCB. It is this feature of the HVQFN package that makes it ideally suited for low voltage, high current DC to DC converter applications.

Electrical connection between the package and the printed circuit board is made by printing solder paste on the printed circuit board, placing the component and reflowing the solder in a convection or infra-red oven. The solder reflow process is shown in [Figure 13](#page-13-0) and the typical temperature profile is shown in [Figure 14](#page-13-1). To ensure good solder joints, the peak temperature  $T<sub>p</sub>$  should not exceed 220 $^{\circ}$  C, and the time above liquidus temperature should be less than 1.25 minutes. The ramp rate during preheat should not exceed 3 K/s. Nitrogen purge is recommended during reflow.

<span id="page-13-1"></span><span id="page-13-0"></span>![](_page_13_Figure_6.jpeg)

### <span id="page-14-0"></span>**14.2 Rework guidelines**

Since the solder joints are largely inaccessible, only the side fillets can be touched up. If there are defects underneath the package, then the whole package has to be removed.

The first step in component removal is to reflow the solder joints. It is recommended that the board is heated from the underside using a convective heater whilst hot air or gas is directed at the upper surface of the component. Nozzles should be used to direct the hot air or gas to minimize heating of adjacent components. Excessive airflow should be avoided since this may cause the package to skew. An airflow of 15 to 20 liters per minute is usually adequate.

Once the solder joints have reflowed, the component should be lifted off the board using a vacuum pen.

The next step is to clean the solder pads using solder braid and a blade shaped soldering tool. Finally, the pads should be cleaned with a solvent. The solvent is usually specific to the type of solder paste used in the original assembly and the paste manufacturers recommendations should be followed.

### <span id="page-14-2"></span><span id="page-14-1"></span>**15. Mounting**

### **15.1 PCB design guidelines**

The terminals on the underside of the package are rectangular in shape with a rounded edge on the inside. Electrical connection between the package and the printed-circuit board is made by printing solder paste onto the PCB footprint followed by component placement and reflow soldering. The PCB footprint shown in [Figure 15](#page-15-0) is designed to form reliable solder joints.

The use of solder resist between each solder land is recommended. PCB tracks should not be routed through the corner areas shown in [Figure 15.](#page-15-0) This is because there is a small, exposed remnant of the lead frame in each corner of the package, left over from the cropping process.

Good surface flatness of the PCB lands is desirable to ensure accuracy of placement after soldering. Printed-circuit boards that are finished with a roller tin process tend to leave small lumps of tin in the corners of each land. Levelling with a hot air knife improves flatness. Alternatively, an electro-less silver or silver immersion process produces completely flat PCB lands.

![](_page_15_Figure_2.jpeg)

### <span id="page-15-1"></span><span id="page-15-0"></span>**15.2 Solder paste printing**

The process of printing the solder paste requires care because of the fine pitch and small size of the solder lands. A stencil thickness of 0.125 mm is recommended. The stencil apertures can be made the same size as the PCB lands in [Figure 15](#page-15-0).

The type of solder paste recommended for HVQFN packages is "No clean", Type 3, due to the difficulty of cleaning flux residues from beneath the package.

# <span id="page-16-0"></span>**16. Revision history**

![](_page_16_Picture_107.jpeg)

# <span id="page-17-3"></span>**17. Data sheet status**

![](_page_17_Picture_224.jpeg)

<span id="page-17-0"></span>[1] Please consult the most recently issued data sheet before initiating or completing a design.

<span id="page-17-1"></span>[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

<span id="page-17-2"></span>[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

# <span id="page-17-4"></span>**18. Definitions**

**Short-form specification —** The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition —** Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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# <span id="page-17-5"></span>**19. Disclaimers**

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![](_page_18_Picture_193.jpeg)

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![](_page_18_Picture_8.jpeg)

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